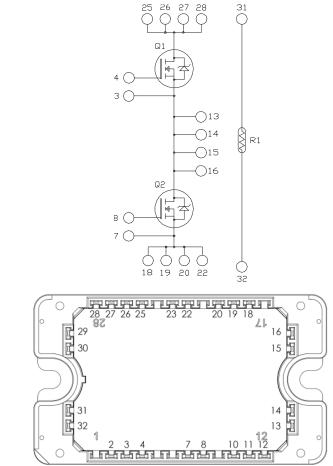


Phase Leg SiC MOSFET Power Module

Product Overview

The MSCSM70AM07T3AG device is a full bridge 700V, 353A phase leg silicon carbide (SiC) MOSFET power module.



Notes:

- Pins 25 to pins 28 must be shorted together
- · Pins 13 to pins 16 must be shorted together
- Pins 18/19/20/22 must be shorted together
- All ratings at T_J = 25 °C, unless otherwise specified.

These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The following are key features of the MSCSM70AM07T3AG device:

- SiC Power MOSFET
 - High speed switching
 - Low R_{DS(on)}
 - Ultra low loss
- Kelvin source for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring
- Aluminum Nitride (AIN) substrate for improved thermal performance

Benefits

The following are the benefits of MSCSM70AM07T3AG device:

- High efficiency converter
- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

Application

The MSCSM70AM07T3AG device is designed for the following applications:

- Welding converters
- · Switched mode power supplies
- Uninterruptible power supplies
- EV motor and traction drive

1. Electrical Specifications

This section provides the electrical specifications of the MSCSM70AM07T3AG device.

1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings per SiC MOSFET of the MSCSM70AM07T3AG device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit
V _{DSS}	Drain-Source voltage		700	V
I _D			353 ¹	A
			281 ¹	
I _{DM}	Pulsed drain current		700	
V _{GS}	Gate-Source voltage		-10/23	V
R _{DS(on)}	Drain-Source ON resistance		6.4	mΩ
P _D	Power dissipation	T _C = 25 °C	988	W

Note:

1. Specification of SiC MOSFET device but output current must be limited due to size of power connectors.

The following table lists the electrical characteristics per SiC MOSFET of the MSCSM70AM07T3AG device.

Table 1-2. Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0V V _{DS} = 700V		—	—	300	μA
R _{DS(on)}	Drain–Source on	V _{GS} = 20V	T _J = 25 °C	_	5	6.4	mΩ
	resistance I _D = 120A	I _D = 120A	T _J = 175 °C	_	6.3		
V _{GS(th)}	Gate threshold voltage	$V_{GS} = V_{DS}$ $I_D = 12 \text{ mA}$		1.9	2.4	—	V
I _{GSS}	Gate–Source leakage current	V _{GS} = 20V; V _{DS} = 0V		_	_	300	nA

Electrical Specifications

The following table lists the dynamic characteristics per SiC MOSFET of the MSCSM70AM07T3AG device.

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance	V _{GS} = 0V		_	13.5	_	nF
C _{oss}	Output capacitance	V _{DS} = 700V			1.5		
C _{rss}	Reverse transfer capacitance	f = 1 MHz .			0.09		
Qg	Total gate charge	$V_{GS} = -5V/20V$			645		nC
Q _{gs}	Gate-Source charge	V _{Bus} = 470V			174		
Q _{gd}	Gate-Drain charge	I _D = 120A			105	_	
T _{d(on)}	Turn-on delay time	V _{GS} = -5V/20V	T _J = 150 °C		40		ns
Tr	Rise time	V _{Bus} = 400V			40	<u> </u>	
T _{d(off)}	Turn-off delay time	I _D = 240A			50		
T _f	Fall time	$R_{G(on)} = 22.7\Omega$ $R_{G(off)} = 1.6\Omega$			20		
Eon	Turn-on energy	V _{GS} = -5V/20V	T _J = 150 °C		2.7		mJ
E _{off}	Turn-off energy	$V_{Bus} = 400V$ $I_D = 240A$ $R_{G(on)} = 22.7\Omega$ $R_{G(off)} = 1.6\Omega$	T _J = 150 °C		0.58		
R _{Gint}	Internal gate resistance			_	1.9	_	Ω
R _{thJC}	Junction-to-case thermal resistance			_	_	0.152	°C/W

Table 1-3. Dynamic Characteristics

The following table lists the body diode ratings and characteristics per SiC MOSFET of the MSCSM70AM07T3AG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V _{SD}	Diode forward voltage	V _{GS} = 0V; I _{SD} = 120A		3.4	_	V
		$V_{GS} = -5V; I_{SD} = 120A$	_	3.8		
t _{rr}	Reverse recovery time	I _{SD} = 120A; V _{GS} = -5V		38		ns
Q _{rr}	Reverse recovery charge	V _R = 470V; di _F /dt = 3000 A/µs		954		nC
I _{rr}	Reverse recovery current			44	_	A

Electrical Specifications

1.2 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM70AM07T3AG device.

Symbol	Characteristics	Characteristics			Max.	Unit
V _{ISOL}	RMS isolation voltage, any term	RMS isolation voltage, any terminal to case t =1 min, 50 Hz/60 Hz			—	V
TJ	Operating junction temperature	Operating junction temperature range			175	°C
T _{JOP}	Recommended junction tempera	Recommended junction temperature under switching conditions			T _{Jmax} –25	
T _{STG}	Storage temperature range	Storage temperature range			125	
T _C	Operating case temperature	Operating case temperature			125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package weight	Package weight			110	g

Table 1-5. Thermal and Package Characteristics

The following table lists the temperature sensor NTC of the MSCSM70AM07T3AG device.

Table 1-6. Temperature Sensor NTC

Symbol	Characteristic		Min.	Тур.	Max.	Unit
R ₂₅	Resistance at 25°C		—	50	—	kΩ
$\Delta R_{25}/R_{25}$	-	—	—	5	_	%
B _{25/85}	T ₂₅ = 298.15 K	—	—	3952		К
ΔB/B	—	T _C = 100 °C	_	4	_	%

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

Note: See APT0406—Using NTC Temperature Sensor Integrated into Power Module for more information.

1.3 Typical SiC MOSFET Performance Curve

This section shows the typical SiC MOSFET performance curves of the MSCSM70AM07T3AG device.



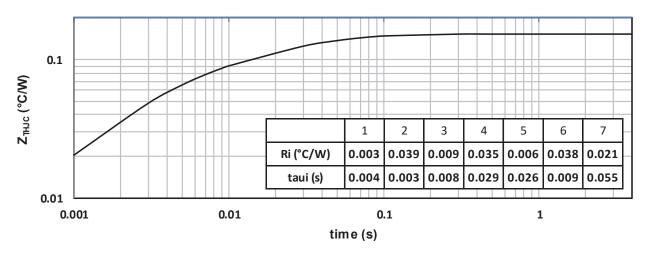
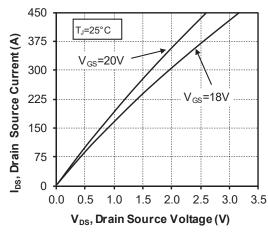


Figure 1-2. Output Characteristics, $T_J = 25 \ ^{\circ}C$





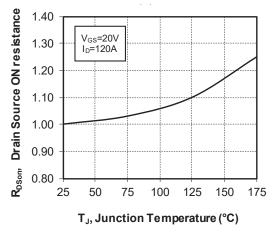
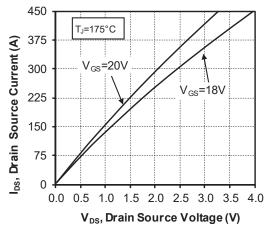
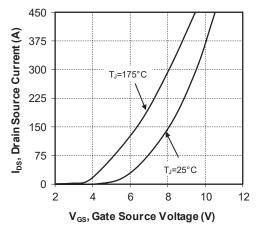


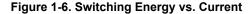
Figure 1-3. Output Characteristics, T_J = 175 °C

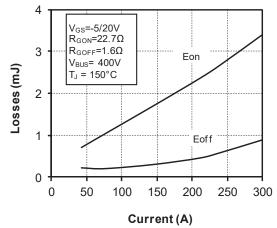


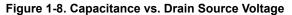


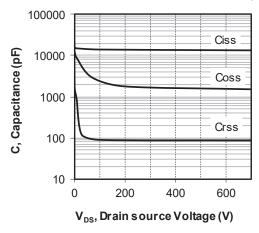


Electrical Specifications











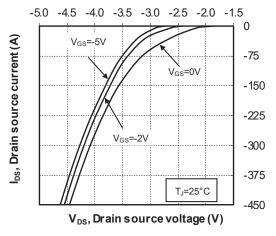


Figure 1-7. Turn On Energy vs. Rg

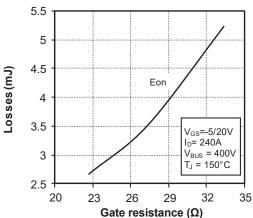
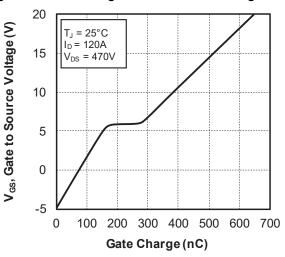
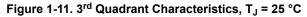
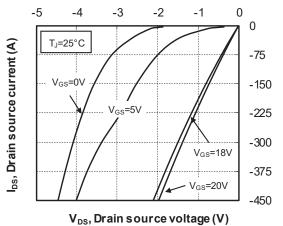


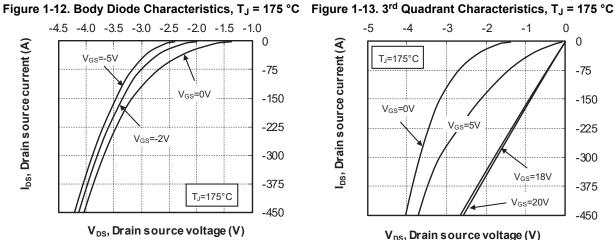
Figure 1-9. Gate Charge vs. Gate Source Voltage

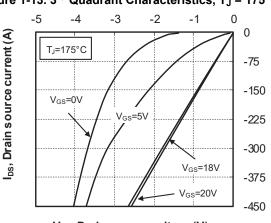






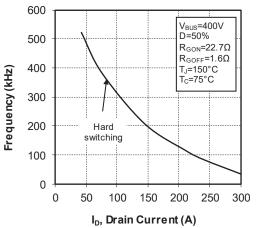
Electrical Specifications

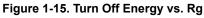


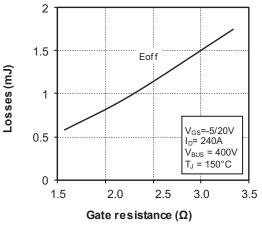


V_{DS}, Drain source voltage (V)

Figure 1-14. Operating Frequency vs Drain Current







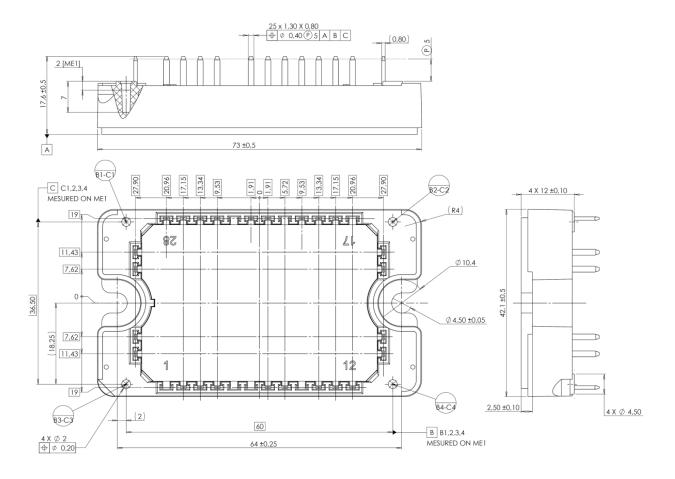
2. Package Specifications

The following section shows the package specification of the MSCSM70AM07T3AG device.

2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM70AM07T3AG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



Note: See AN3500A—Mounting instructions for SP1F and SP3F power modules for more information.

3. Revision History

Revision	Date	Description
Α	06/2022	Initial Revision

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